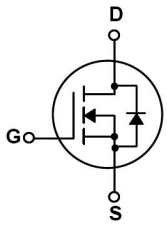
TO-220FL N 700V

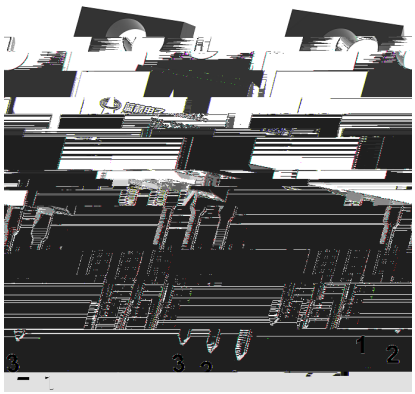
N-CHANNEL 700V Super-Junction Power MOSFET in a TO-220FL Plastic Package.

$R_{DS(on)}$×Qg 100% RoHS

Very low $R_{DS(on)}$×Qg,100% avalanche tested,RoHS compliant, HF product.

For switch mode power supply, uninterruptible power supply, power factor correction.





PIN1 G PIN 2 D PIN 3 S

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	700	V
Drain Current	I_D(Tc=25)	7	A
Drain Current - Pulsed	I_{DM}	28	A
Gate-Source Voltage	V_{GS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	200	mJ
Avalanche Current	I_{AS}	6.1	A
Power Dissipation	P_D(Tc=25)	31	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	
Junction-to-Case	$R_{\theta JC}$	4	/W
Junction-to-Ambient	$R_{\theta JA}$	62.5	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	700	745		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=700V V_{GS}=0V T_J=25			1.0	μA
Gate-Body Leakage Current, Forward	I_{GSS}	V_{GS}=±30V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250μA	2.5	3.4	4.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=3.5A		495	600	mΩ
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_{SD}=7A T				

Parameter Symbol

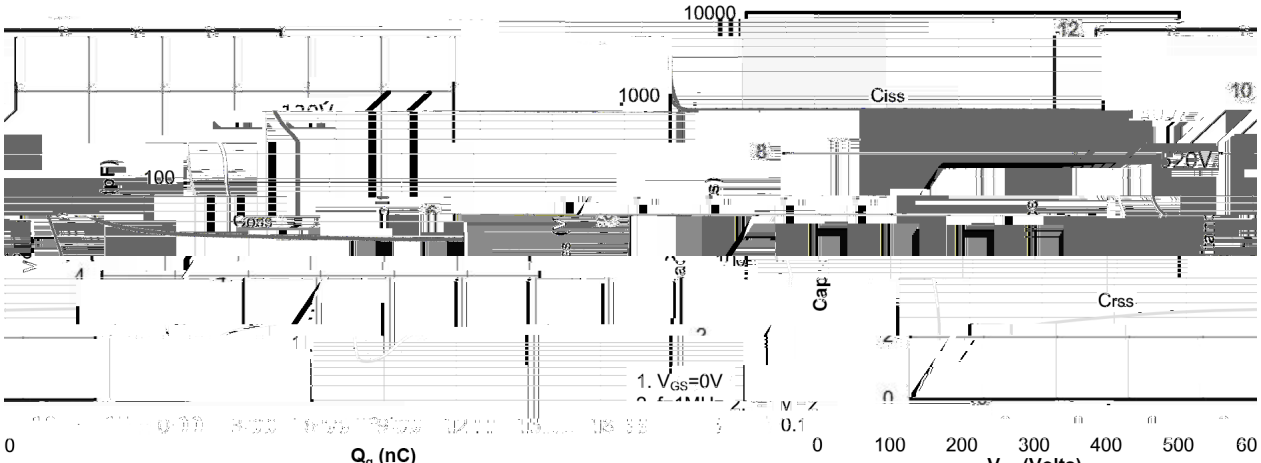


Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

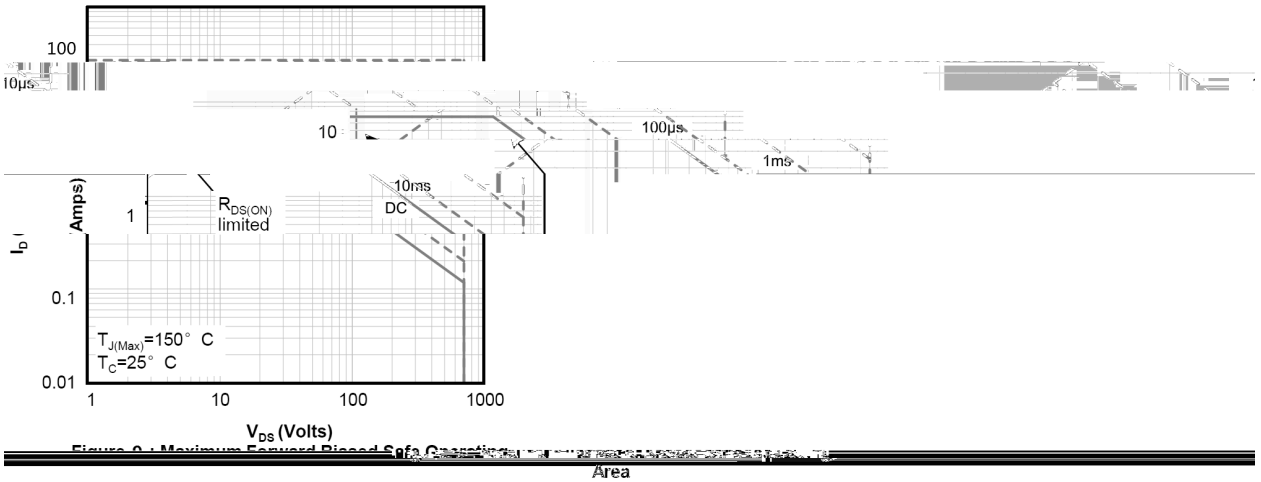
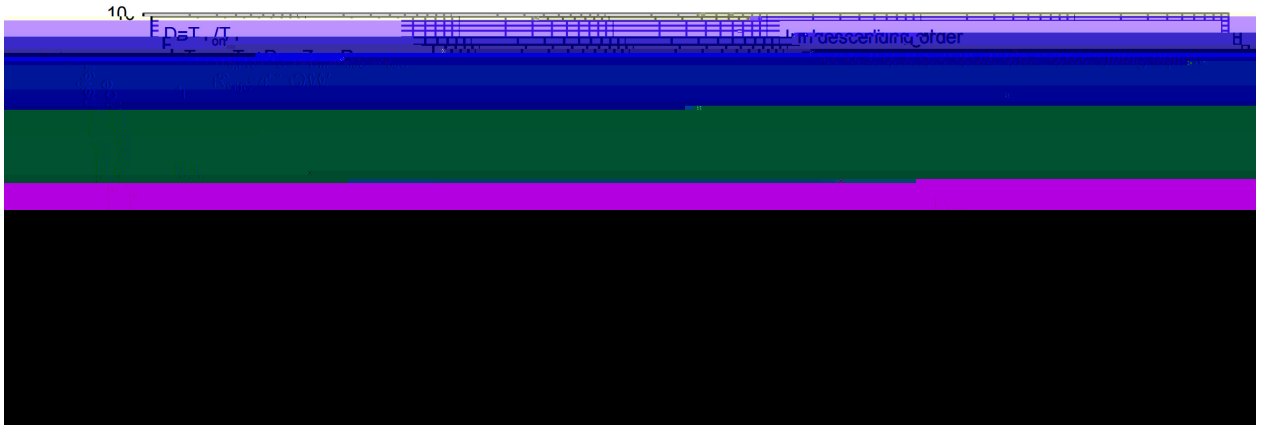
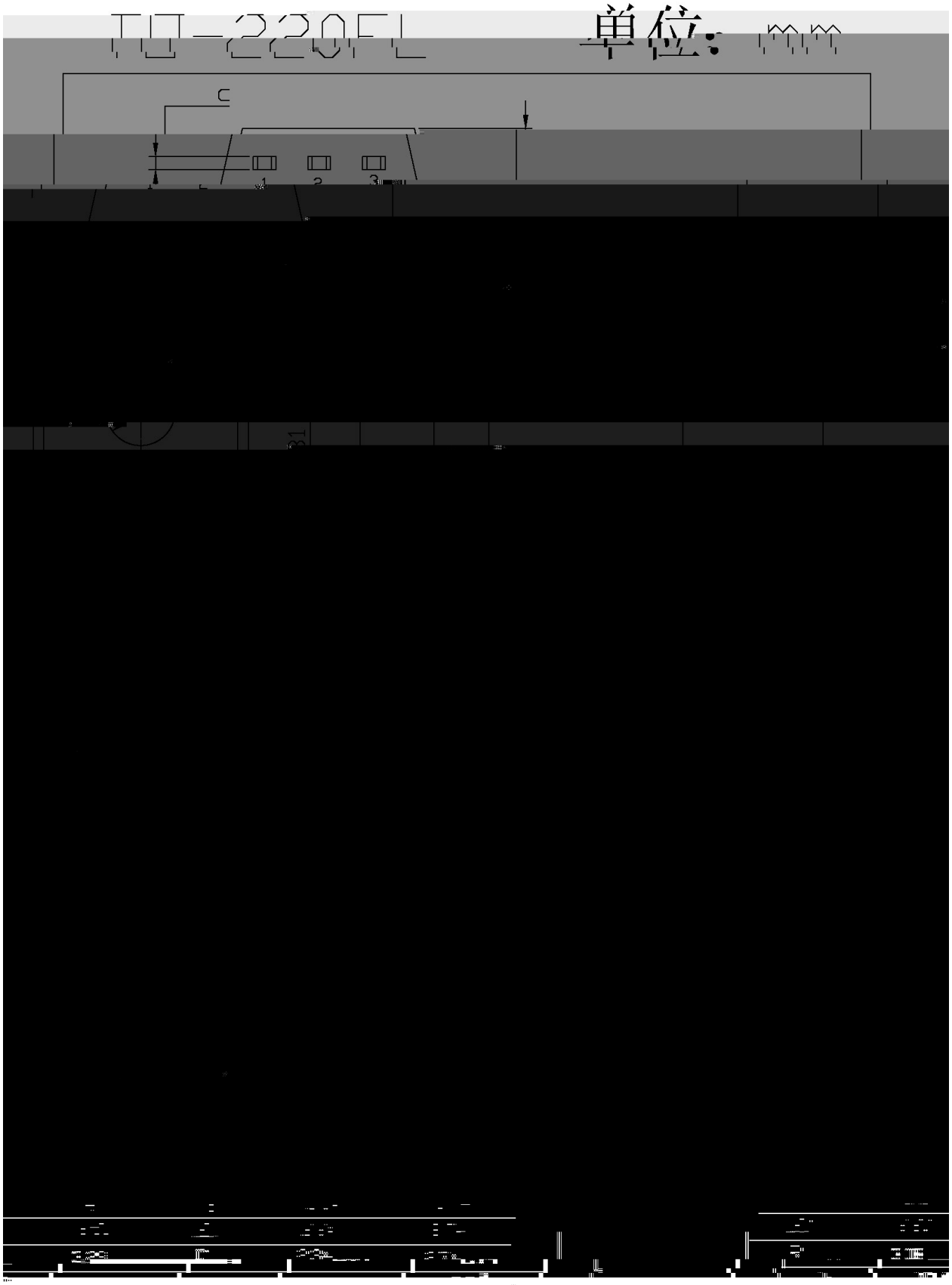
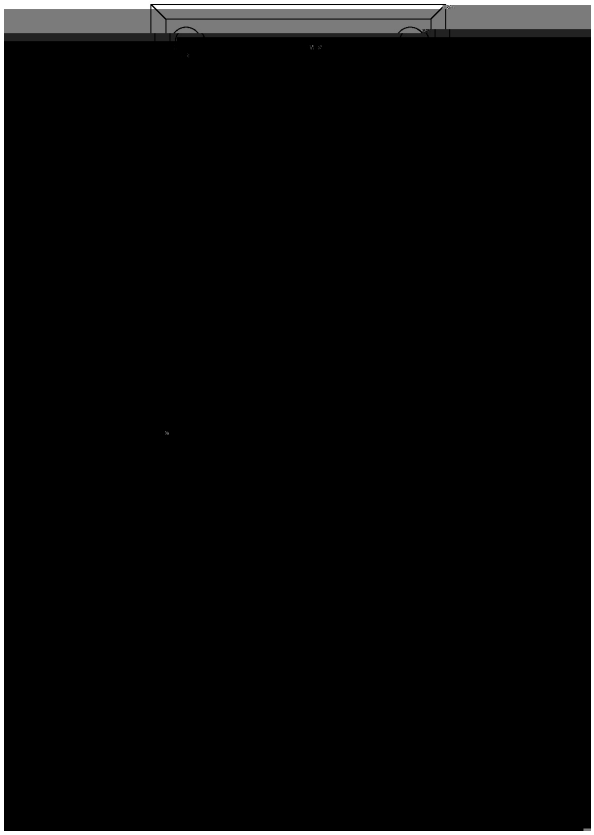


Figure 9 : Maximum Forward Biased Safe Operating Area



TO-220FL 单位：mm





BR

70R600C

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Note:

BR:	Company Code
70R600C:	Product Type Code
****:	Lot No. Code, code change with Lot No